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a passivation film covering the surface of the semiconductor substrate and the wirings, including a first insulating film that contains a [at least one impurity selected from the group consisting of argon,] boron impurity [, nitrogen and phosphorus].

26. (As filed) The semiconductor device according to claim 25, wherein the passivation film includes a second insulating film, located on at least one of an upper side and a lower side of the first insulating film, having a hygroscopicity lower than that of the first insulating film.

27. (As filed) The semiconductor device according to claim 26, wherein the second insulating film is selected from the group consisting of silicon nitride film, silicon oxide film and silicon oxynitride film.

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28. (Amended) The semiconductor device according to claim 25, wherein organic components in the first insulating film have been decomposed by said boron [the at least one selected] impurity.

29. (As filed) The semiconductor device according to claim 28, wherein the passivation film includes a second insulating film, located on at least one of an upper side and a lower side of the first insulating film, having a hygroscopicity lower than that of the first insulating film.

30. (As filed) The semiconductor device according to claim 29, wherein the second insulating film is selected from the group consisting of silicon nitride film, silicon oxide film and silicon oxynitride film.

31. (As filed) The semiconductor device according to claim 25, wherein the first insulating film includes an inorganic SOG (Spin-on-Glass) film.

32. (As filed) The semiconductor device according to claim 31, wherein the passivation film includes a second insulating film, located on at least one of an upper side and a lower side of the first insulating film, having a hygroscopicity lower than that of the first insulating film.